

MH 185 Hall-effect sensor is a temperature stable, stress-resistant, micro-power latch. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

The MH 185 includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, and a short circuit protected open-drain output. Advanced CMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

This device requires the presence of both south and north polarity magnetic fields for operation. In the presence of a south polarity field of sufficient strength, the device output latches on, and only switches off when a north polarity field of sufficient strength is present.

The MH 185 is rated for operation between the ambient temperatures –40°C and 125°C for the K temperature range. The two package styles available provide magnetically optimized solutions for most applications. Package SO is an SOT-23, a miniature low-profile surface-mount package, while package UA is a three-lead ultramini SIP for through-hole mounting.

The package type is in a lead (Pb)-free version was verified by third party Lab.

#### Features and Benefits

- Micro-Power Latch function down to 8uA (Avg) supply current
- CMOS Hall IC Technology
- Solid-State Reliability
- Bipolar Output CMOS latch
- Operation down to 2.5V
- High Sensitivity Latch for direct "two reed switch application" replacement.
- Micro-power consumption for battery-powered applications
- 100% tested at 125 °C for K spec/ Wide range of working Temperature
- RoHS is qualified by 3 party lab

#### **Applications**

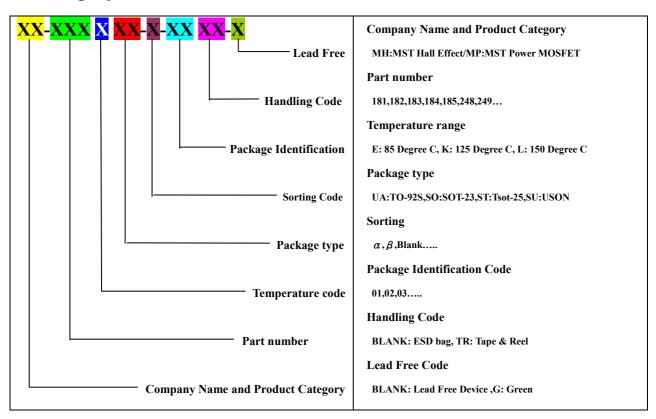
- Solid state high sensitivity latch function
- High sensitivity, latch function for "2 reed switch" replacement in low duty cycle applications.
- Revolution counter in battery-powered applications
- Water Meter RPM detector



#### MH 185

#### CMOS Micro-power Latch

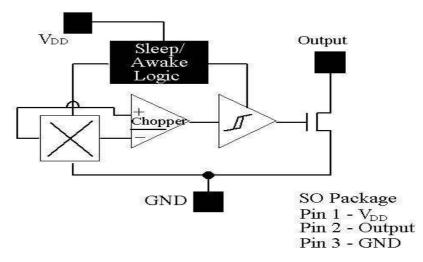
#### **Ordering Information**



Part No.	<b>Temperature Suffix</b>	Package Type	Package Identification
185	K (-40°C to + 125°C)	<b>UA (TO-92S)</b>	01
	K (-40°C to + 125°C)	<b>SO (SOT-23)</b>	05

KUA spec is using in industrial and automotive application. Special Hot Testing is utilized.

#### Functional Diagram



Note: Static sensitive device; please observe ESD precautions. Reverse  $V_{DD}$  protection is not included. For reverse voltage protection, a  $100\Omega$  resistor in series with  $V_{DD}$  is recommended.

Absolute Maximum Ratings

Supply Voltage (Operating), V <sub>DD</sub>	5V		
Supply Current (Fault), I <sub>DD</sub>	1mA		
Output Voltage, V <sub>OUT</sub>	5V		
Output Current (Fault), I <sub>OUT</sub>	5mA		
Operating Temperature Range, T <sub>A</sub>	-40°C to +125°C		
Storage Temperature Range, T <sub>S</sub>	-55°C to +150°C		

### MH-185 Electrical Specifications

DC operating parameters:  $T_A = 25^{\circ}C$ ,  $V_{DD}=3V_{DC}$  (unless otherwise specified).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Supply Voltage	$V_{DD}$	Operating	2.5		5	V
Supply Current	$I_{DD}$	Average		8		μΑ
Output Current	I <sub>OUT</sub>				1.0	mA
Saturation Voltage	$V_{SAT}$	$I_{OUT} = 1 \text{mA}$			0.4	V
Awake mode	$T_{AW}$	Operating		175		us
Sleeping mode	$T_{SL}$	Operating			70	ms

#### Magnetic Specifications

DC operating parameters:  $T_A = 25^{\circ}C$ ,  $V_{DD}=3V_{DC}$  (unless otherwise specified).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Operating Point	B <sub>OP</sub>		-6.0	-3.5	-0.5	mT
Release Point	$B_{RP}$		+0.5	+3.5	+6.0	mT
Hysteresis	$B_{HYS}$			7.0		mT

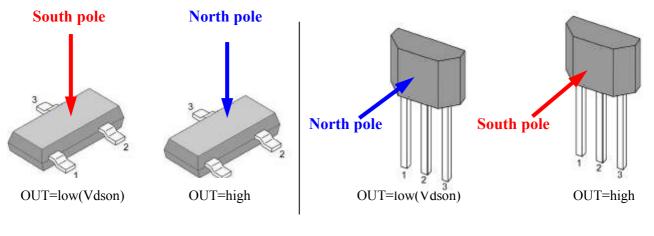
**Note:** 1 mT = 10 Gauss.

### Output Behaviour versus Magnetic Pole

DC Operating Parameters Ta = -40 to  $125^{\circ}$ C, Vdd = 2.5 to 5V (unless otherwise specified)

Parameter	Test condition(SO)	OUT(SO)	Test condition(UA)	OUT(UA)
South pole	B>Bop	low	B <brp< td=""><td>high</td></brp<>	high
North pole	B <brp< td=""><td>high</td><td>B&gt;Bop</td><td>Low</td></brp<>	high	B>Bop	Low

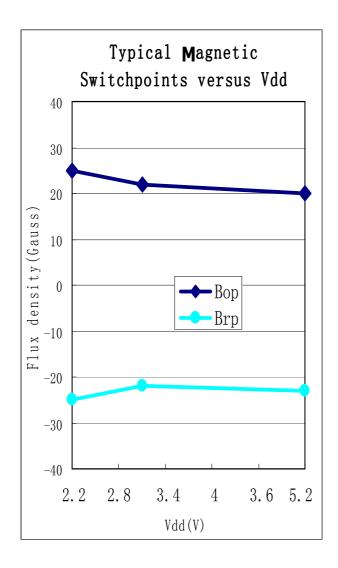


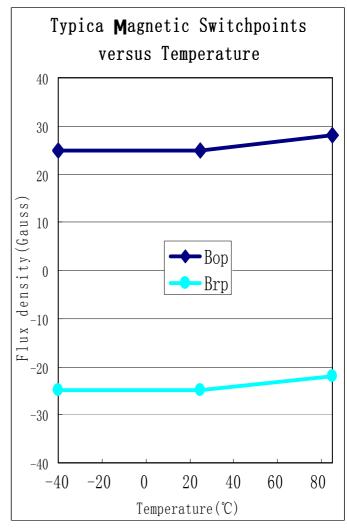


### SO package

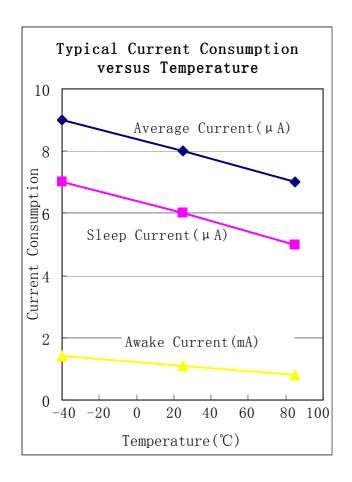
**UA** package

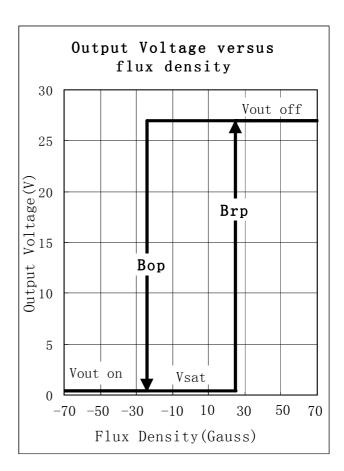
#### Performance Graphs



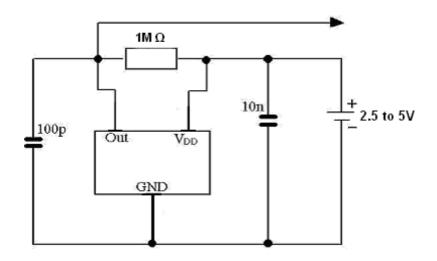




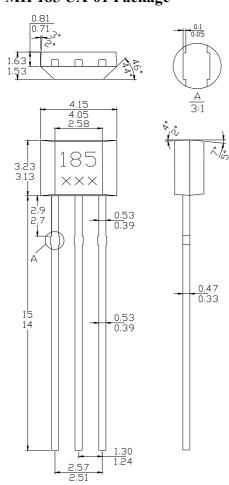




#### Typical Application



## **Package Physical Characteristics and sensor location** MH 185 UA-01 Package



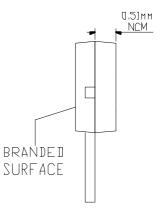
#### **NOTES:**

- 1).Controlling dimension: mm
- 2).Leads must be free of flash and plating voids
- Do not bend leads within 1 mm of lead to package interface.
- 4).PINOUT:

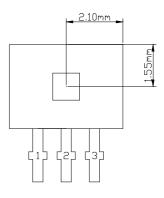
Pin 1 VDD

Pin 2 GND

Pin 3 Output



Active Area Depth

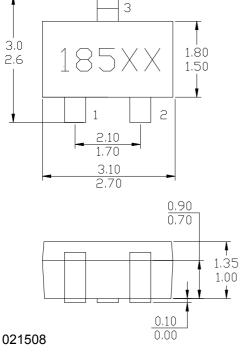


Sensor Location

#### MH 185 SO-05 Package

#### (Top View)

0.50 0.35



## NOTES:

1. PINOUT (See Top View at left:)

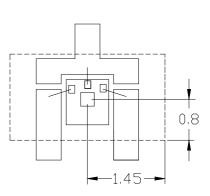
Pin 1 VDD

Pin 2 Output

Pin 3 GND

- 2. Controlling dimension: mm;
- Lead thickness after solder plating will be 0.254mm maximum.

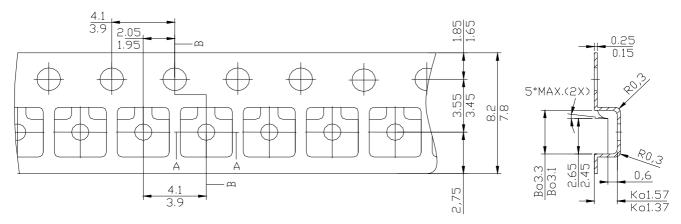
## SOT-23 Hall Plate / Chip Location (Bottom view)

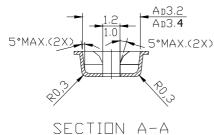


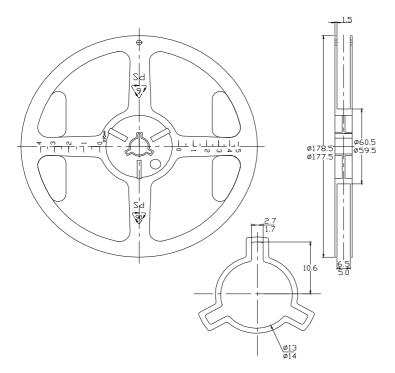
### MH 185

#### CMOS Micro-power Latch

## Sot 23 Tape on Reel dimension







#### **NOTES:**

- 1. Material: Conductive polystyrene;
- 2. DIM in mm;
- 10 sprocket hole pitch cumulative tolerance ±0.2;
- 4. Camber not to exceed 1mm in 100mm;
- Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole;
- 6. (S.R. OHM/SQ) Means surface